

1/4

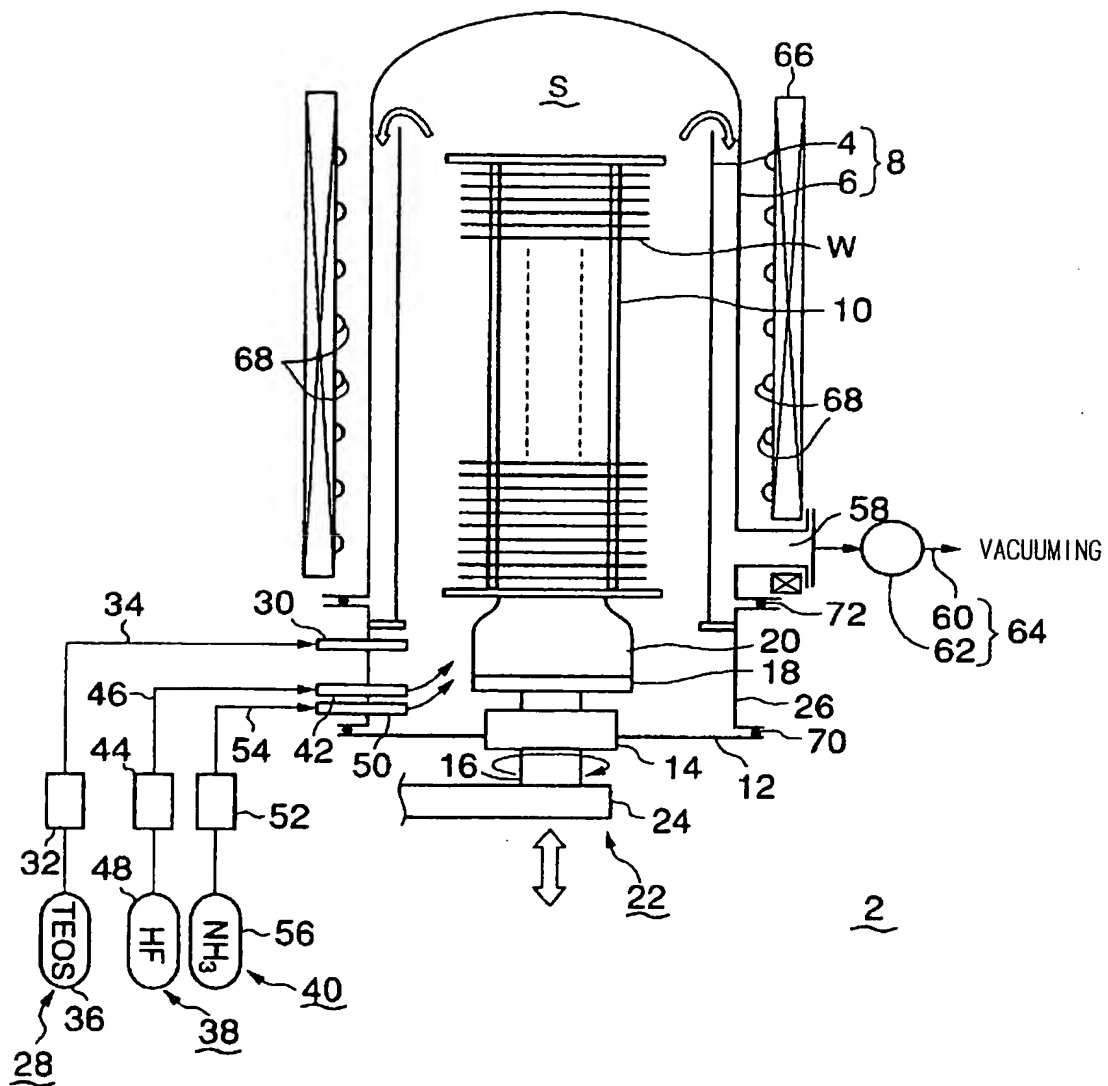


FIG. 1

ETCHING RATE OF SILICON OXIDE FILM FORMED BY TEOS			ETCHING RATE OF QUARTZ MATERIAL			EVALUATION
	TEMPERATURE [°C]	PRESSURE [Torr]	HF [sccm]	NH ₃ [sccm]	[nm/min]	[nm/min]
METHOD ACCORDING TO PRESENT INVENTION	300	400	182	1820	0.6	15.9
	300	400	1000	1000	26.8	69.1
	300	400	1820	182	96.6	196.6
CONVENTIONAL METHOD	300	400	1820	0	0.4	170.1
						×

FIG. 2

3/4

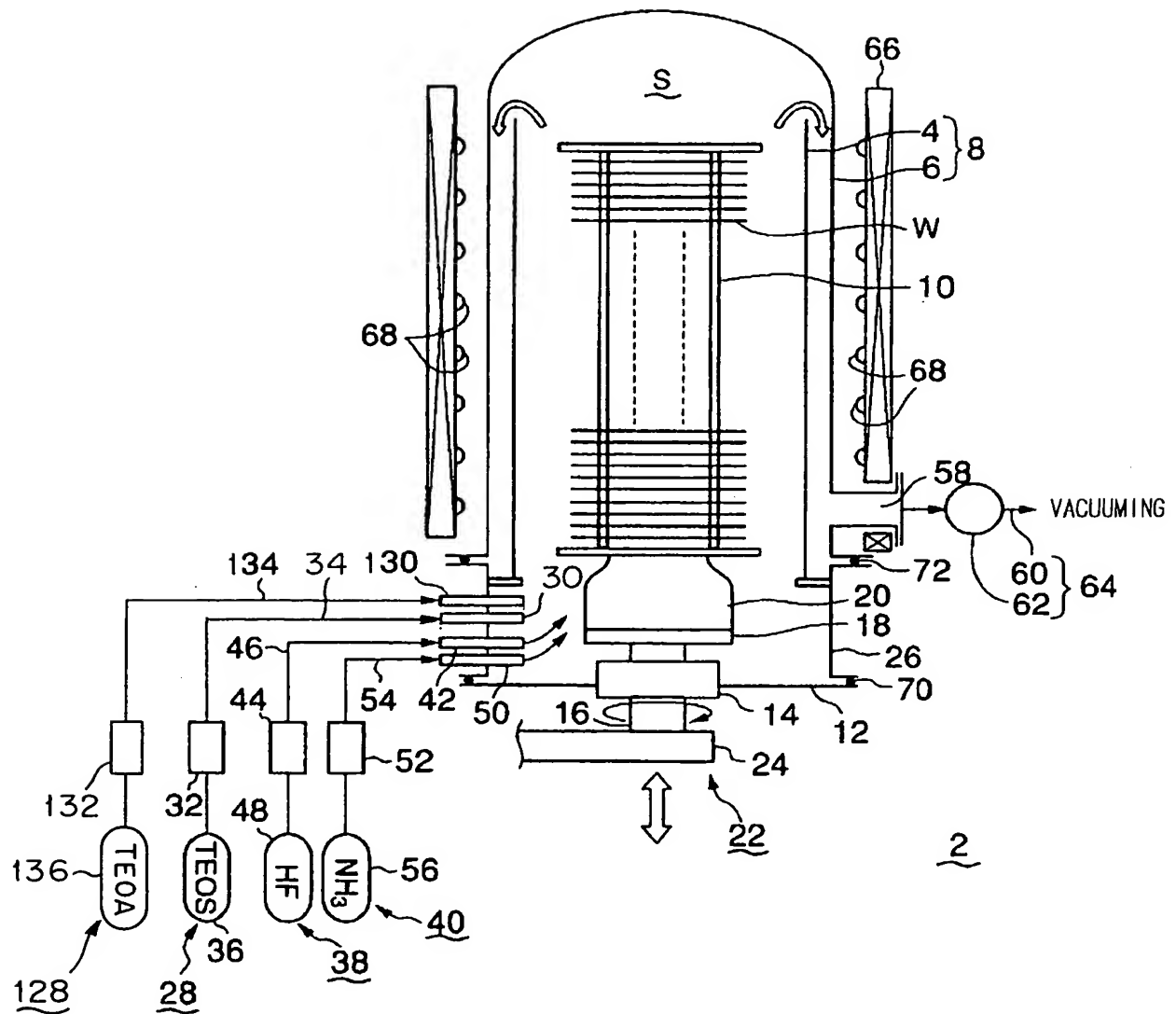


FIG. 3

4/4

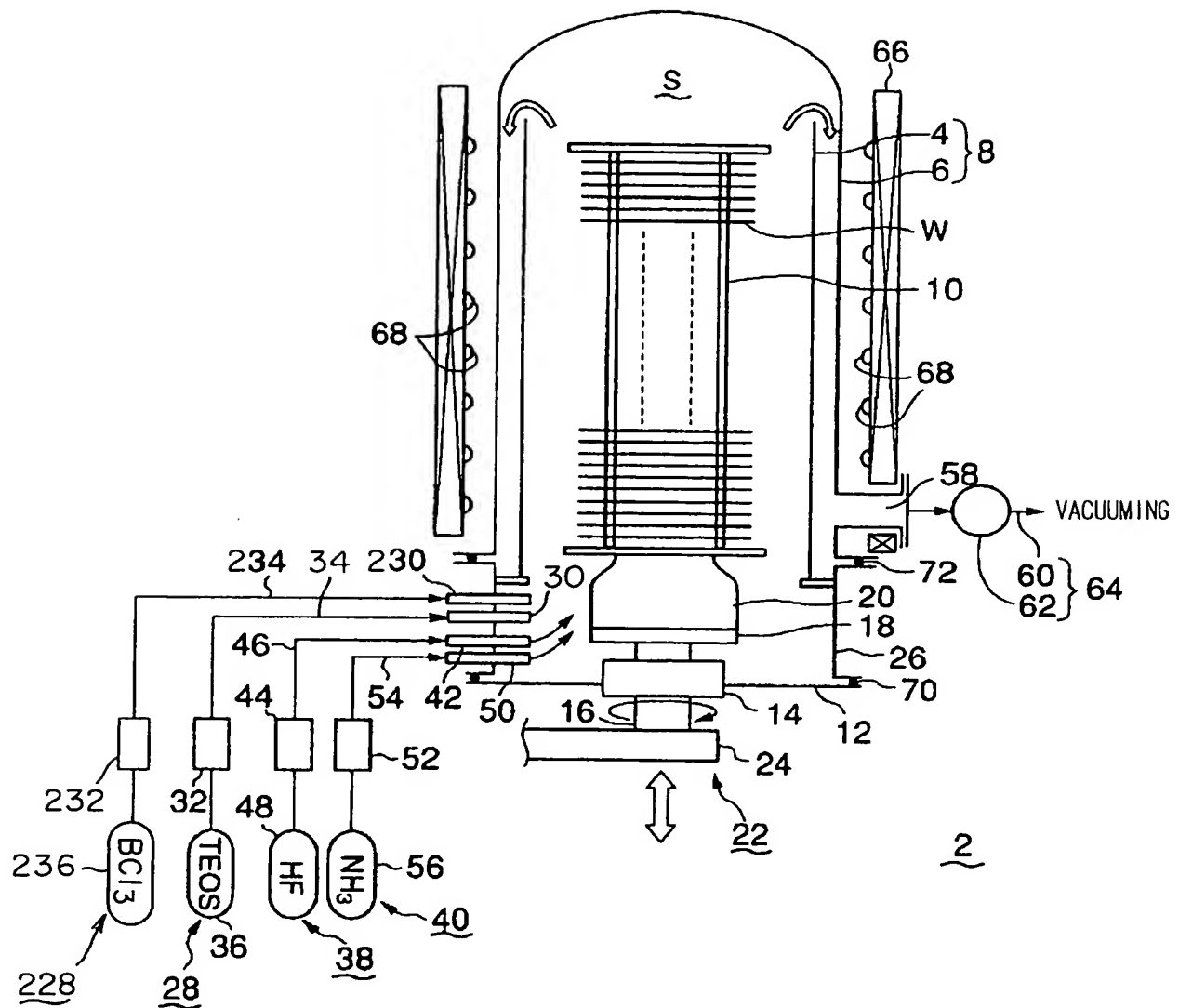


FIG. 4